TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

## HN1K06FU

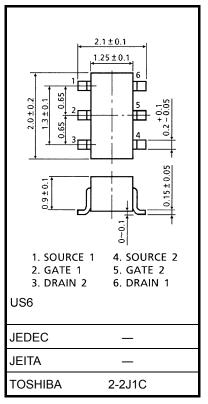
# High Speed Switching Applications Analog Switch Applications

Unit: mm

- High input impedance and extremely low drive current.
- $V_{th}$  is low and it is possible to drive directly at low-voltage CMOS. :  $V_{th}$  = 0.5 to 1.5 V
- · Switching speed is fast.
- · Suitable for high-density mounting because of a compact package

# Absolute Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	$V_{DS}$	20	V	
Gate-source voltage	$V_{GSS}$	10	V	
Drain current	ΙD	100	mA	
Drain power dissipation	P <sub>D</sub> (Note 1)	200	mW	
Channel temperature	T <sub>ch</sub>	150	°C	
Storage temperature range	T <sub>stg</sub>	-55 to 150	°C	



Weight: 6.8 mg

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

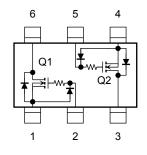
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: TOTAL rating

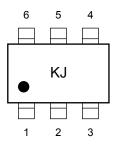
## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = 10 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	1	μА
Drain-source breakdown voltage	V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0 \ V$	20	_	_	V
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	_	_	1	μА
Gate threshold voltage	$V_{th}$	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.5	_	1.5	V
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$	35	62	_	mS
Drain-source ON resistance	R <sub>DS</sub> (ON)	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	3.5	6.0	Ω
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 3 V, V <sub>GS</sub> =0 V, f = 1 MHz	_	14	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 3 V, V <sub>GS</sub> =0 V, f = 1 MHz	_	5.3	_	pF
Output capacitance	Coss	V <sub>DS</sub> = 3 V, V <sub>GS</sub> =0 V, f = 1 MHz	_	16	_	pF
Switching time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0 \text{ to } 2.5 \text{ V}$	_	0.28	_	0
	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0 \text{ to } 2.5 \text{ V}$	_	0.34		μS

## **Equivalent Circuit (top view)**



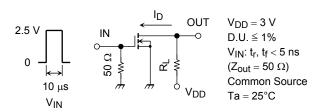
## Marking



(Q1, Q2 common)

#### **Switching Time Test Circuit**

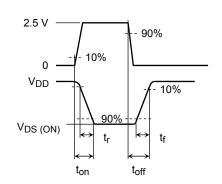
#### (a) Test circuit



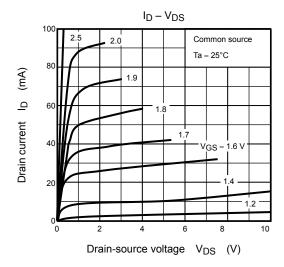
#### (b) $V_{\text{IN}}$

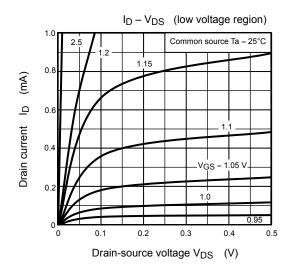
 $v_{\rm GS}$ 

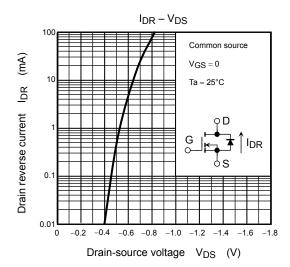


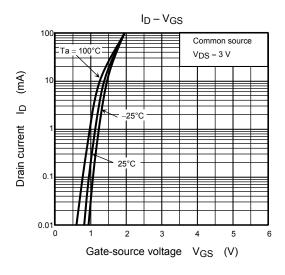


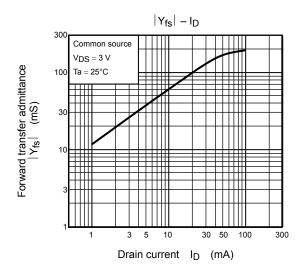
(Q1, Q2 common)

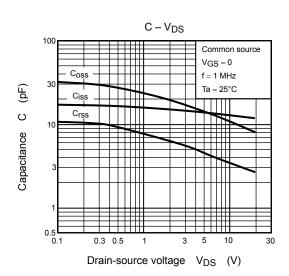




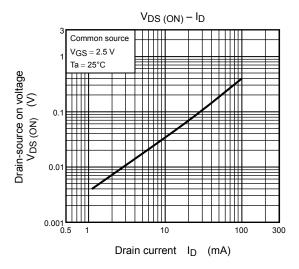


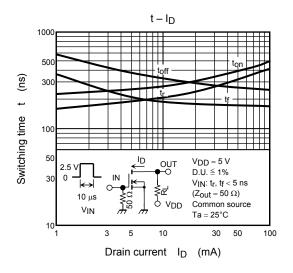


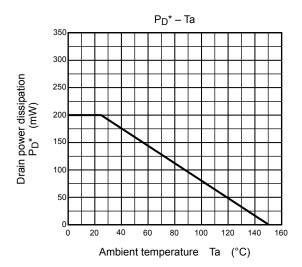




(Q1, Q2 common)







\*: TOTAL rating

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20070701-EN GENERAL

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